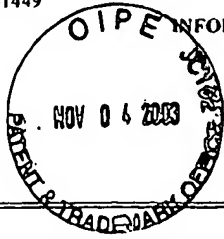


Form PTO-1449



**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

~~09786,022~~

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
PK	3,171,068	02/23/65	Denkwalter et al.	317	234	10/19/60
	3,925,803	12/09/75	Kobayashi	357	22	07/12/73
	3,961,356	06/01/76	Okuhara et al.	357	50	10/31/74
	4,003,072	01/11/77	Matsushita et al.	357	52	11/01/74
	4,055,884	11/01/77	Jambotkar	29	571	12/13/76
	4,072,975	02/07/78	Ishtiani	357	23	04/22/77
	4,101,922	07/18/78	Tihanyi	357	23	03/09/77
	4,145,700	03/20/79	Jambotkar	357	23	08/08/77
	4,320,410	03/16/82	Nishizawa et al.	357	43	05/03/79
	4,345,265	08/17/82	Blanchard	357	23	04/14/80
	4,366,495	12/28/82	Goodman et al.	357	23	08/06/79
	4,376,286	03/08/83	Lidow et al.	357	23	02/09/81
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 053 854 B1	16.06.82	EPO	H01L	29/06	x
	GB 2 089 118 A	16.02.82	UK	H01L	29/78	x
	EP 0 069 429 A2	12.01.83	EPO	H01L	29/78	x
	EP 0 447 873 A2	01.04.92	EPO	H01L	29/784	x
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	1967	A.S. Grove: "Physics and Technology of Semiconductor Devices" p 78-83
	1976	B. Jayant Baliga, Sorab K. Ghandi: "Analytical Solutions for the Breakdown Voltage of Abrupt Cylindrical and Spherical Junctions" (p 739-744)
	1977	Richard F. David: "Computerized Thermal Analysis of Hybrid Circuits" 27th Electronics Components Conference, May 16-18 1977 (p 324-332)

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7/16/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449

**INFORMATION DISCLOSURE CITATION
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(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

09786,822

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
<i>KA</i>	4,404,575	09/13/83	Nishizawa	357	22	05/03/82
	4,417,385	11/29/83	Temple	29	571	09/09/82
	4,561,003	12/24/85	Tihanyi et al.	357	23.4	04/13/84
	4,593,302	06/03/86	Lidow et al	357	23.4	08/18/80
	4,748,103	05/31/88	Hollinger	430	314	03/21/66
	4,754,310	06/28/88	Coe	357	13	12/04/84
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	4,895,810	01/23/90	Meyers et al.	431	41	05/17/88
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO
	EP 0 772 244 A1	07.05.97	EPO	H01L	29/78	x
	DE 196 04 043 A1	5.2.96	Germany	H01L	29/78	x
	WO 97/29518	14.08.97	PCT	H01L	29/78	x
	DE 196 04 044 A1	5.2.97	Germany	H01L	29/78	x
	WO 97/35346	25.09.97	PCT	H01L	29/78	x
	EP 0 834 926 A3	08.26.98	EPO	H01L	29/08	x
	DE 197 30 759 C1	17.7.97	Germany	H01L	29/78	x
	WO 99/04437	28.01.99	PCT	H01L	29/78	x
	WO 99/23703	14.05.99	PCT	H01L	29/06	x
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IEEE	1979	Chenming Hu: "A Parametric Study of Power MOSFETS" (p 988-998)
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DATE CONSIDERED

7/16/04

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Form PTO 449 E

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

09/786,022

10/633 044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
PA	4,914,058	04/03/90	Blanchard	437	203	12/29/87	
	4,926,226	05/15/90	Heremans et al.	357	27	09/06/88	
	4,941,026	07/10/90	Temple	357	23.4	08/26/88	
	4,974,059	11/27/90	Kinzer	357	23.4	08/28/89	
	4,975,782	12/04/90	Bauer	357	38	02/22/89	
	4,994,871	02/19/91	Chang et al.	357	23.4	12/02/88	
	5,008,725	04/16/91	Lidow et al.	357	23.4	12/23/88	
	5,010,025	04/23/91	Solomon	437	29	04/03/89	
	5,019,522	05/28/91	Meyer et al.	437	29	01/02/90	
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	5,072,269	12/10/91	Heida	357	23.6	03/15/89	
	5,089,434	02/18/92	Hollinzer	437	41	01/22/90	
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	WO99/36961	22.07.99	PCT	H01L	23/48		x
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	EP 0 939 446 A1	01/09/99	EPO	H01L	29/08		x
	WO 00/14807	16.03.00	PCT	H01L	29/78		x
	DE 198 40 032 C1	2.9.98	Germany	H01L	29/78		x
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IEEE	1979	Chenming Hu article, "Optimum Doping Profile for Minimum Ohmic Resistance and High-Breakdown Voltage"

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DATE CONSIDERED

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Form PTO-1449

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

Docket Number (Optional)

068758.0102

Application Number

00786,022

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
Pd	5,126,807	06/30/92	Baba et al.	357	23.4	06/12/91	
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	5,231,474	07/27/93	Hollinger	257	355	07/17/92	
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	5,340,315	07/04/95	Rumennik	257	331	10/11/94	
	5,438,215	08/01/95	Tihyani	257	401	03/25/94	
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation <hr/> YESNO	
	WO 00/02250	13.01.00	PCT	H01L	29/10		x
	EP 0 973 203 A2	19.01.00	EPO	H01L	29/06		x
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			Tihyani and Krauss, SIPMOS, Elektronik 1980, pg. 61-64
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	UMI	December 1981	Richard A. Blanchard: "Optimization of Discrete High Power MOS Transistors"

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Form PTO-1449

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~~09786,022~~

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

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PA	5,473,180	12/05/95	Ludikhuizen	257	336	07/11/94
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	5,648,283	07/15/97	Tsang et al.	437	40	01/31/94
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	5,973,360	10/26/99	Tihanyi	257	330	09/21/98
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	US2001/0050549		Deboy et al.	323	313	03/12/01
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Transition YES NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

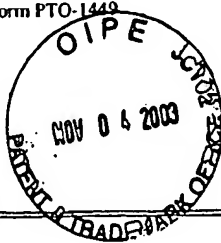
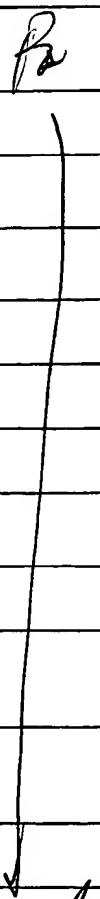
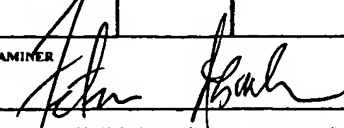
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	IEEE	1982	Chen and Hu article, "Optimum Doping Profile of Power MOSFET Epitaxial Layer"
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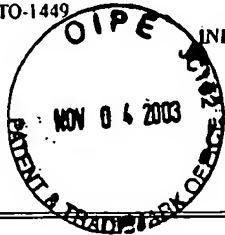
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Sheet 6 of 8

Form PTO-1449 				INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		Docket Number (Optional) 068758.0102		Application Number 00786,022 10/633084	
						Applicant Deboy et al.			
						Filing Date 04/22/99		Group Art Unit:	
U.S. PATENT DOCUMENTS									
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE			
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO			
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	IEEE	April 1987	Daisuke Ueda, Hiromitsu Takagi, Gota Kano: An Ultra-Low On-Resistance Power MOSFET Fabricated by Using a Fully Self-Aligned Process						
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EXAMINER 				DATE CONSIDERED 7/16/04					
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Form PTO-1449



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Docket Number (Optional)

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Application Number

09786,022

10/633044

Applicant Deboy et al.

Filing Date 04/22/99

Group Art Unit:

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	Translation YES NO

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		May 1998	Article, "Siemens' new MOSFET design drastically cuts on-state resistance"
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DATE CONSIDERED

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Docket Number (Optional)

Application Number

068758.0102

~~09786,022~~

Deboy et al.

Filing Date 04/22/99

Group Art Unit:

**EXAMINER
INITIAL**

**DOCUMENT
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DATE _____

NAME**CLASS**

**SUB-
CLASS**

**FILING DATE IF
APPROPRIATE**

**DOCUMENT
NUMBER**

DATE _____

COUNTRY

CLASS

SUB-
CLASS

Translation

YES

NO

(Including Author, Title, Date, Pertinent Pages, Etc.)

1998

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X.B. Chen et al. "High voltage sustaining structure with embedded oppositely doped regions"

Lai, et al.; "Characteristics and Utilization of a New Class of Low On-Resistance MOS-Gated Power Device" (1999)

July 1999

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Chinese
Journal of
Semiconductors

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June 2000

Chen article, "Optimization of the Specific On-Resistance of the CoolMOS," published by IEEE Transactions on Electron Devices

EXAMINER

DATE CONSIDERED

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INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number: 26615	ATTORNEY'S DKT No. H1174		APPLICATION No. Unassigned	
			APPLICANT(S) Chih-Yuh Yang et al.			
			FILING DATE August 4, 2003		GROUP Unassigned	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.
	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.
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	Co-pending U.S. Application Serial Number 10/348,758 filed January 23, 2003 entitled, "GERMANIUM MOSFET DEVICES AND METHODS FOR MAKING SAME," Judy Xilin An et al., 22 page specification, 29 sheets of drawings.

EXAMINER 	DATE CONSIDERED 7/28/04
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INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number 26615	ATTORNEY'S DKT No. H1174		APPLICATION No. 10/633,034		
			APPLICANT(S) Chih-Yuh Yang et al				
			FILING DATE August 4, 2003		GROUP Unassigned		
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>fb</i>	6,525,403 B2	02-25-03	Inaba et al.	257	618	09-24-01	
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>fb</i>	U.S. Patent Application Publication No. US 2003/0113970 A1 ; June 19, 2003; Fried et al.						
<i>fb</i>	U.S. Patent Application Publication No. US 2003/0042531 A1; March 6, 2003; Lee et al.						
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>7/20/04</i>			

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